

1 **Effect of metastable Mg₂Si and dislocations on α -Al(MnFe)Si dispersoid formation in Al-**
2 **Mn-Mg 3xxx alloys**

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8

9 **Abstract**

10 The effect of metastable Mg₂Si and dislocations on the formation of α -Al(MnFe)Si
11 dispersoids in Al-Mn-Mg 3xxx alloys were studied by a close examination of the dispersoid
12 precipitation process using the quench technique and TEM observation. Special attention was
13 paid to the nucleation mechanisms. Mg plays an important role in promoting the formation of α -
14 Al(MnFe)Si dispersoids. The number density and volume fraction of the dispersoids in the Mg
15 containing alloy are much higher than those in the control alloy without Mg, resulting in a strong
16 dispersoid strengthening effect. During the heating process in the Mg containing alloy,
17 metastable Mg₂Si precipitated and dissolved, leaving local Si-rich areas on pervious metastable
18 Mg₂Si, which provide favorable nucleation sites for α -Al(MnFe)Si dispersoids. It was found that
19 β' -Mg₂Si precipitates were more effective at the promotion of the dispersoid nucleation than β'' -
20 Mg₂Si. In the deformed sample, the dislocations become the preferable sites for the α -
21 Al(MnFe)Si dispersoid nucleation. By reducing dispersoid free zones, the dispersoid distribution
22 became more uniform compared to the non-deformed sample. The dispersoid nucleation
23 mechanisms based on both metastable Mg₂Si and dislocations are proposed and discussed.
24

25 **Keywords:** Al-Mn-Mg 3xxx alloys; Dispersoid precipitation; Nucleation mechanism;
26 Microstructure; TEM observation
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30 1. Introduction

31 Traditional Al-Mn-Mg 3xxx alloys are widely used for architecture, packaging and
32 automobile applications due to their excellent corrosion resistance, formability and weldability.
33 Though 3xxx alloys are normally classified as non-heat-treatable alloys, a strong dispersoid
34 strengthening effect has been discovered in recent years by applying a suitable heat treatment [1-
35 5]. Formed during heat treatment, α -Al(MnFe)Si dispersoids are the key strengthening phase in
36 the aluminum matrix, which greatly improves the strength of 3xxx alloys, particularly at elevated
37 temperature [6]. α -Al(MnFe)Si dispersoids have a partial coherence with the aluminum matrix
38 [4, 7] and are thermally stable up to 573 K (300 °C) [1, 3, 8], which leads 3xxx alloys to be
39 promising candidates for elevated temperature applications .

40 During heating process of the heat-treatment, metastable Mg_2Si could precipitate in some
41 Al-Mn-Mg-Si alloys because of the presence of Mg and Si. The precipitation sequence of Mg_2Si
42 in Mg and Si containing aluminum alloys was generally described as follows: Mg and Si clusters
43 \rightarrow needle-like β'' - Mg_2Si \rightarrow lath-like or rod-like β' - Mg_2Si \rightarrow plate-like equilibrium β - Mg_2Si [9-
44 14]. The typical size of the needle-like β'' - Mg_2Si precipitates is in the range of 4 x 4 x 50 nm
45 [11]. The lath-like or rod-like β' - Mg_2Si precipitates have dimensions of approximately 10 x 10 x
46 500 nm [12]. The size of the plate-like equilibrium β - Mg_2Si phase can reach to several
47 micrometers [9, 15, 16]. It was reported in previous studies [17-20] that metastable Mg_2Si
48 precipitates could have a positive effect on the nucleation of α -Al(MnFeCr)Si and α -AlMnSi
49 dispersoids in 6xxx alloys. It was observed during the dispersoid formation [18] that there
50 existed an intermediate phase, the u-phase, that first nucleated on the β' - Mg_2Si and that the α -
51 Al(MnFeCr)Si dispersoids heterogeneously nucleated on these 'u-phase' precipitates. However,
52 the effect of metastable Mg_2Si on the nucleation of Mn-containing dispersoids has not been
53 systematically investigated.

54 It is well known that some defects, such as vacancies and dislocations, may enhance the
55 precipitation kinetics of the secondary precipitation phase due to the increasing number of
56 nucleation sites and diffusivities of the alloying elements in the materials [21-26]. There were a
57 few reports that documented the precipitation behavior of dispersoids in deformed 3xxx alloys
58 [27, 28], in which the plastic deformation increased the number density and volume fraction of
59 the dispersoids. This could be attributed to the increase of nucleation sites and diffusion rate by
60 dislocations. It is worth mentioning that the above reported alloys did not contain Mg, and thus,

61 no Mg₂Si existed. This suggests that the dislocations in the deformed samples could have an
62 impact on dispersoid nucleation in addition to the possible Mg₂Si nucleation effect.

63 In our previous work [29], the effects of Mg and Si on α -Al(MnFe)Si dispersoid
64 precipitation, elevated-temperature strength and creep resistance in 3xxx alloys were
65 systematically studied, in which there was an evidence that pre-existing β' -Mg₂Si could promote
66 the formation of α -Al(MnFe)Si dispersoids. The aim of the present work is to clarify the effects
67 of metastable Mg₂Si and dislocations on the nucleation and growth of α -Al(MnFe)Si dispersoids
68 in the Al-Mn-Mg 3xxx alloys. The influence of metastable Mg₂Si on the nucleation of the
69 dispersoids was investigated by a close examination of the dispersoid precipitation process using
70 the quench technique and TEM observation. The effect of different types of metastable Mg₂Si on
71 the dispersoid formation was also evaluated using two-step heat treatments. Moreover, the effect
72 of dislocations on the nucleation of dispersoids in the deformed samples was studied and
73 compared to the non-deformed control sample.

74

75 **2. Experimental procedures**

76 Two experimental Al-Mn-Mg 3xxx alloys were used in this study. The base alloy, used as a
77 control material, contains 1.25%Mn, 0.25%Si and 0.6%Fe (all of the alloy compositions are in
78 wt% unless indicated otherwise). The main alloy investigated contains additionally 1%Mg, while
79 the concentrations of Mn, Si and Fe remain the same as in the base alloy. The two alloys were
80 prepared from commercially pure Al (99.7%), and Mg (99.9%), and Al-25%Mn, Al-25%Fe and
81 Al-50%Si master alloys. The chemical compositions of the experimental alloys were analyzed
82 using an optical emission spectrometer and are listed in Table 1. In each test, approximately 3 kg
83 of material was prepared in a clay-graphite crucible using an electric resistance furnace. The
84 temperature of the alloy melt was maintained at 1032 K (750 °C) and then degassed for 15
85 minutes. The melt was then poured into a pre-heated permanent steel mold. The dimension of the
86 cast ingot is 30 x 40 x 80 mm.

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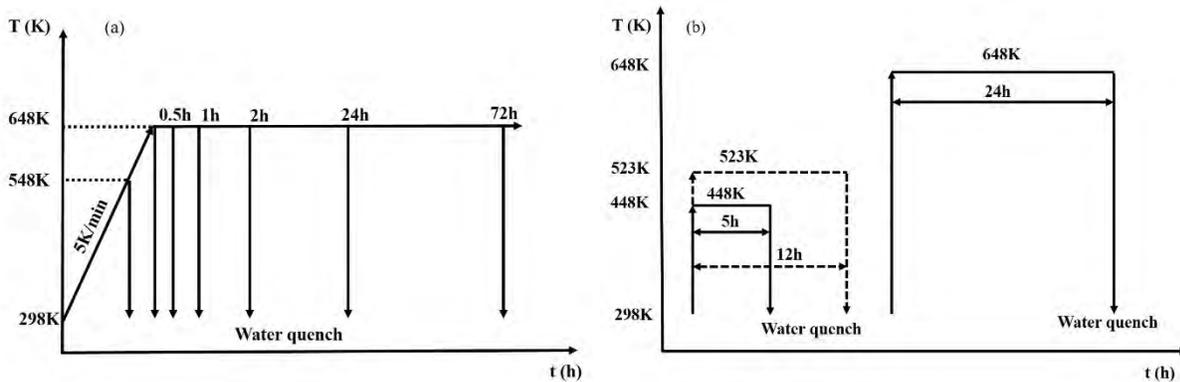
Table 1 Chemical composition of experimental alloys (wt%)

Alloy code	Si	Fe	Mn	Mg	Al
Base	0.23	0.56	1.23	0.002	Bal.
M1	0.26	0.57	1.25	1.00	Bal.

88

89 To examine the influence of metastable Mg_2Si and dislocations on the dispersoid
90 nucleation, the as-cast or deformed samples were heat-treated under different heat treatment
91 procedures. In procedure A, the samples were heated with a constant heating rate of 5 K/min in
92 an electrical resistance furnace from room temperature to the desired temperature. Samples were
93 heated to either 548 K (275 °C) or 648 K (375 °C), or in some cases held at 648 K (375 °C) for
94 various holding times, followed by water quench to room temperature. A schematic diagram of
95 the heat treatment is shown in Fig. 1a. Procedure B is the two-step heat treatment, in which the
96 samples were directly put in the furnace at 448 K (175 °C) for 5 hours and 523 K (250 °C) for 12
97 hours respectively, followed by water quench to room temperature. Then, the samples were put
98 into a furnace directly at 648 K (375 °C) and held for 24 hours followed by water quench (see
99 Fig. 1b).

100



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102

103 **Fig. 1** Schematic diagram of various heat treatments (a) procedure A and (b) procedure B (two-
104 step heat treatment).

105 For the deformation test, the samples were machined to a cylindrical form with 15 mm in
106 length and 10 mm in diameter. In the tests, the samples were cold-compressed to 0.2 true strain at
107 a strain rate of $10^{-3} s^{-1}$ on a Gleeble 3800 thermomechanical testing machine.

108 After heat treatment, the samples were prepared using the conventional metallographic
109 method. The polished samples were etched by 0.5% HF for 20 seconds to reveal the dispersoids.
110 An optical microscope equipped with an imaging analysis system (Clemex PE 4.0) was used to
111 observe the distribution of the dispersoids and to quantify the dispersoid free zone (DFZ). Vicker

112 hardness was measured by an NG-1000 CCD microhardness test machine with a load of 200 g
 113 and a dwell time of 20 s. A transmission electron microscope (TEM, JEM-2100) equipped with
 114 an energy dispersive X-ray spectroscopy (EDS) was used to observe the dispersoids in details.
 115 TEM foils were prepared in a twin jet electropolisher using a solution of 30% nitric acid in
 116 methanol at -20 °C. To evaluate of the dispersoid volume fraction, the thicknesses of TEM foils
 117 were measured using the electron energy loss spectroscopy (EELS) equipped on the TEM. The
 118 size and number density of the dispersoids were measured by using imaging analysis (Clemex
 119 PE 4.0) on the TEM images. The volume fraction of dispersoids, V_v , was calculated using Eq. 1
 120 [6].

$$121 \quad V_v = A_A \frac{K\bar{D}}{K\bar{D}+t} (1 - A_{DFZ}) \quad (1)$$

122 where A_A is the area percentage of dispersoids measured with TEM images and \bar{D} is the average
 123 equivalent diameter of dispersoids from the TEM images; t is the TEM foil thickness; A_{DFZ} is the
 124 area percentage of dispersoid free zone; and K is the shape factor of dispersoids and its value of
 125 0.45 was taken from [6], in which the morphology of dispersoids in AA3xxx alloys was similar
 126 to the morphology of dispersoids in the present work.

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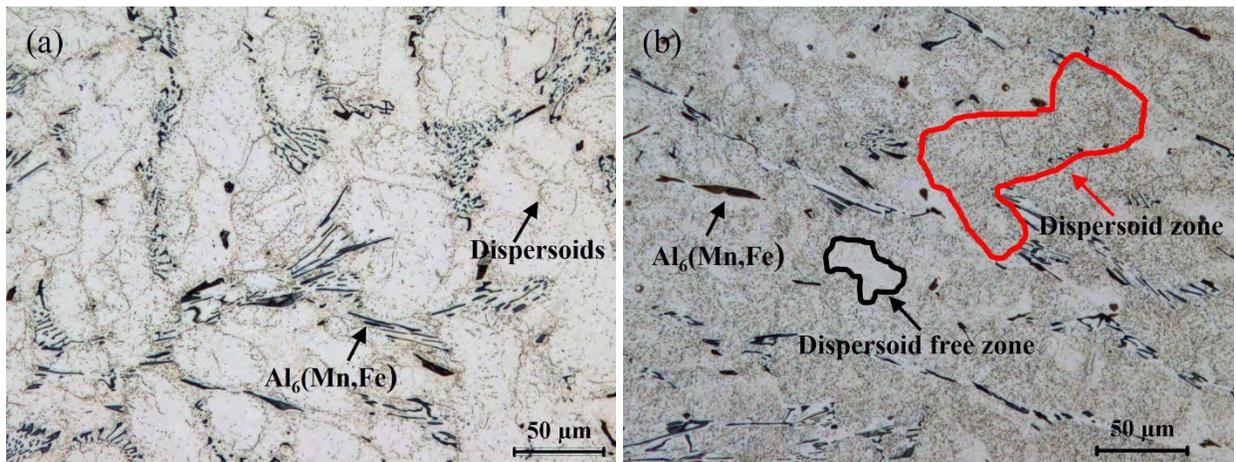
128 **3. Results and discussion**

129 3.1 Precipitation of α -Al(MnFe)Si dispersoids in the base alloy

130 Fig. 2 shows the typical microstructure of the base alloy (Mg-free) after heat treatment at
 131 648 K (375 °C) for 24 h and at 648 K (375 °C) for 72 h. The large needle-like and plate-like
 132 particles are $Al_6(Mn,Fe)$ intermetallics, which originate from the as-cast microstructure and are
 133 distributed in interdendrite regions. The small black dots are α -Al(MnFe)Si dispersoids, which
 134 precipitated during the heat treatment and were revealed after etching with 0.5% HF. The
 135 $Al_6(Mn,Fe)$ and α -Al(MnFe)Si phases were identified in the previous work [1]. After heat-
 136 treatment at 648 K (375 °C) for 24 h, only a few of the dispersoids appeared around intermetallic
 137 particles, which left an extensive dispersoid free zone (DFZ) in the microstructure, as shown in
 138 Fig. 2a. With a prolonged heat treatment up to 72 h (Fig. 2b), more dispersoids precipitated out
 139 of the matrix. However, the amount of dispersoids precipitated is still limited. The area fraction
 140 of DFZ after 648 K (375 °C) for 24 h reached as high as 79%, while the area fraction of DFZ
 141 after 648 K (375 °C) for 72 h still remained at 51.4%. Fig. 3 shows the TEM bright field images,
 142 which displays the dispersoids in details. The α -Al(MnFe)Si dispersoids have cubic-like or rod-

143 like morphologies with a composition close to $Al_{12-20}(MnFe)_3Si$. In the sample treated 648 K
144 (375 °C) for 24 h (Fig. 3a), the number density of the dispersoids was very low and the size was
145 quite large (~97 nm in diameter). After a longer, 72 h treatment (Fig. 3b), the number density of
146 the dispersoids moderately increased and the size slightly decreased to 80 nm. The volume
147 fraction of dispersoids after 648 K (375 °C) for 24 h was only 0.32% and it increased to 0.82%
148 after 648 K (375 °C) for 72 h. After solidification, there was a supersaturated solid solution of
149 Mn and Si in the aluminum matrix, which tended to decompose for dispersoid precipitation
150 during heat treatment. Results indicate that the precipitation of α -Al(MnFe)Si dispersoids in the
151 base alloy was very difficult. After 24 h at 648 K (375 °C), only a small amount of dispersoids
152 (0.32%) precipitated, and the amount was still limited even after a prolonged 72 h treatment.

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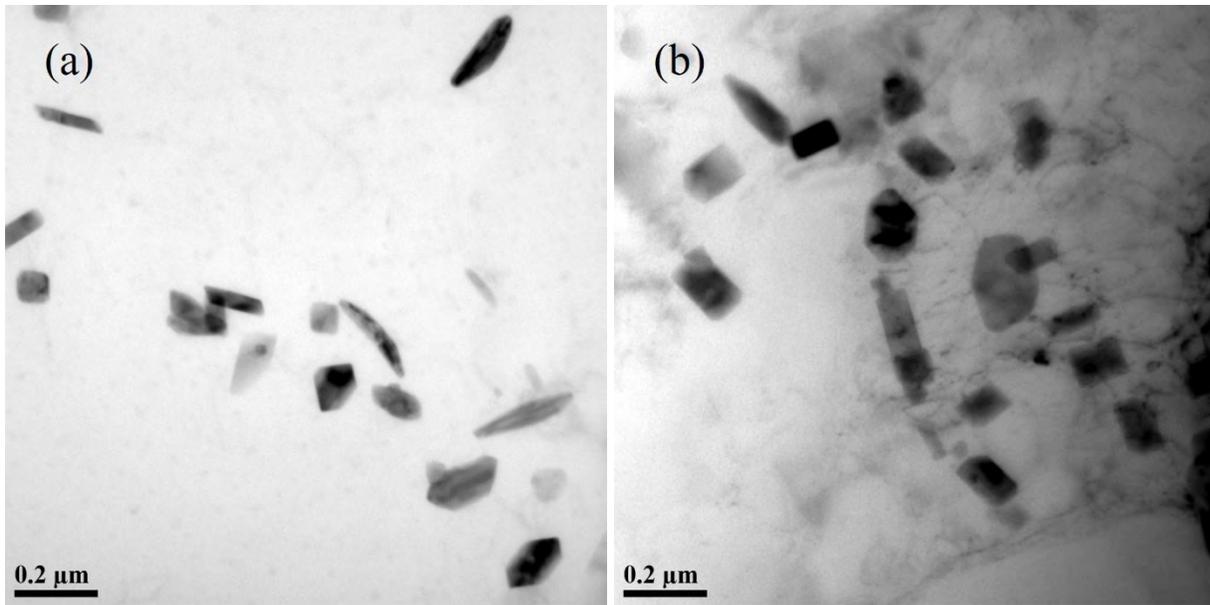


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156 **Fig. 2** Optical images showing the dispersoid distribution in the base alloy, (a) 648 K (375 °C)
157 for 24 h and (b) 648 K (375 °C) for 72 h.

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161 **Fig. 3** TEM bright field images showing the dispersoids in the base alloy, (a) 648 K (375 °C) for
162 24 h and (b) 648 K (375 °C) for 72 h, recorded near [001]_{Al} zone axis.

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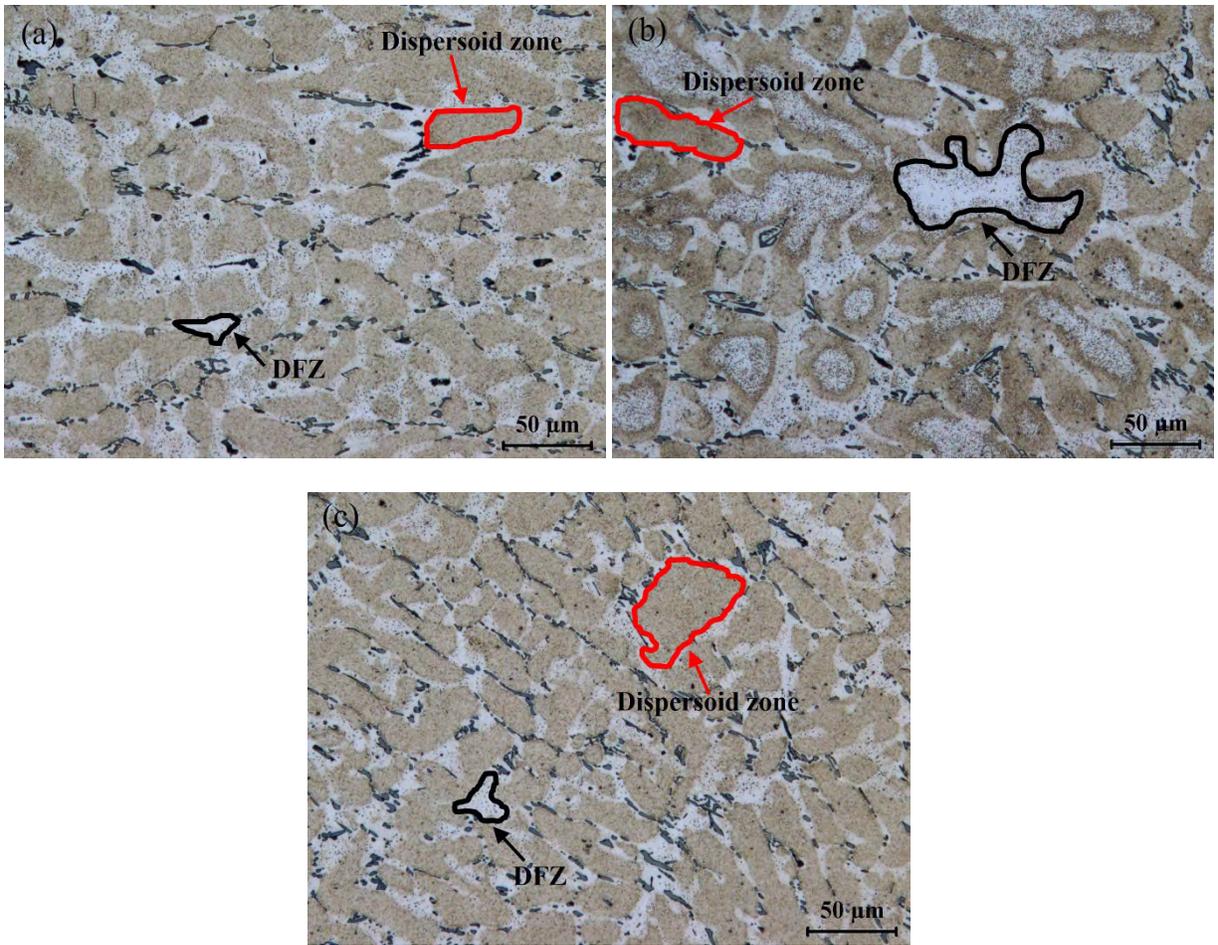
164 3.2 Precipitation of α -Al(MnFe)Si dispersoids in the M1 alloy

165 The precipitation of α -Al(MnFe)Si dispersoids in the Mg containing alloy (M1) after 648 K
166 (375 °C) for 24 h is shown in Fig. 4a. The dispersoid zone and dispersoid free zone (DFZ) were
167 clearly distinguishable in the optical microstructure after etching, as shown in Fig. 4. The
168 dispersoid zones were centered inside aluminum cells and grains, while the DFZs were located in
169 the interdendrite regions close to the Mn-containing intermetallic particles. With the addition of
170 1% Mg, a large number of the dispersoids appeared in the microstructure after heat treatment and
171 the precipitation of dispersoids became much easier when compared to the Mg-free base alloy
172 under the same heat treatment condition. The area fraction of the DFZ decreased from 79% in the
173 base alloy to 26.5% in the M1 alloy. TEM observations (Fig. 5a) confirmed that a large number
174 of rod-like or plate-like dispersoids precipitated in the dispersoid zone. The number density and
175 volume fraction of the dispersoids in the M1 alloy were much higher than in the base alloy. It is
176 evident that the presence of Mg greatly promoted the formation of dispersoids.

177 The typical microstructure of the M1 alloy after the two-step heat treatments
178 (448K(175°C)/5h + 648K(375°C)/24h and 523K(250°C)/12h + 648K(375°C)/24h) are shown in
179 Fig. 4b and c, respectively. Compared to the 448K(175°C)/5h + 648K(375°C)/24h treatment, the

180 sample that underwent the 523K(250°C)/12h + 648K(375°C)/24h treatment showed an increased
181 amount of dispersoids and an reduced DFZ. TEM images (Fig. 5b and c) clearly revealed that the
182 number density of dispersoids in the 448K(175°C)/5h + 648K(375°C)/24h sample was smaller
183 than the one step sample (Fig. 5a), and the number density of dispersoids in the
184 523K(250°C)/12h + 648K(375°C)/24h sample increased. All measured results are shown in Table
185 2. The results show that the area fraction of the DFZ decreases from 30% (448K(175°C)/5h +
186 648K(375°C)/24h) to 23% (523K(250°C)/12h + 648K(375°C)/24h). On the other hand, the
187 volume fraction of dispersoids increases from 1.93% (448K(175°C)/5h + 648K(375°C)/24h) to
188 2.15% (523K(250°C)/12h + 648K(375°C)/24h). It is apparent that the 448K(175°C)/5h +
189 648K(375°C)/24h treatment is less efficient at promoting the dispersoid precipitation than the
190 523K(250°C)/12h + 648K(375°C)/24h treatment. It was reported that during the heating process
191 both metastable β'' -Mg₂Si and β' -Mg₂Si could precipitate in alloys containing Mg and Si
192 depending on the heating rate [11, 12]. To obtain the controllable β'' -Mg₂Si or β' -Mg₂Si
193 precipitation in the samples, the two-step heat treatments with the first step at 448K(175°C)/5h
194 for β'' -Mg₂Si and at 523K(250°C)/12h for β' -Mg₂Si were designed and conducted in the present
195 work. The effect of variants of the metastable Mg₂Si precipitates on the formation of dispersoids
196 and their mechanisms will be discussed later. It is worth to mention that the samples with holding
197 at 448K (175 °C) and particularly at 523K (250 °C) for 12 h can reduce the supersaturated Mn
198 solutes in the aluminum matrix. Therefore, it is expected the volume fraction of the dispersoids
199 formed in the two-step treatments is moderately lower than that in the one step treatment.

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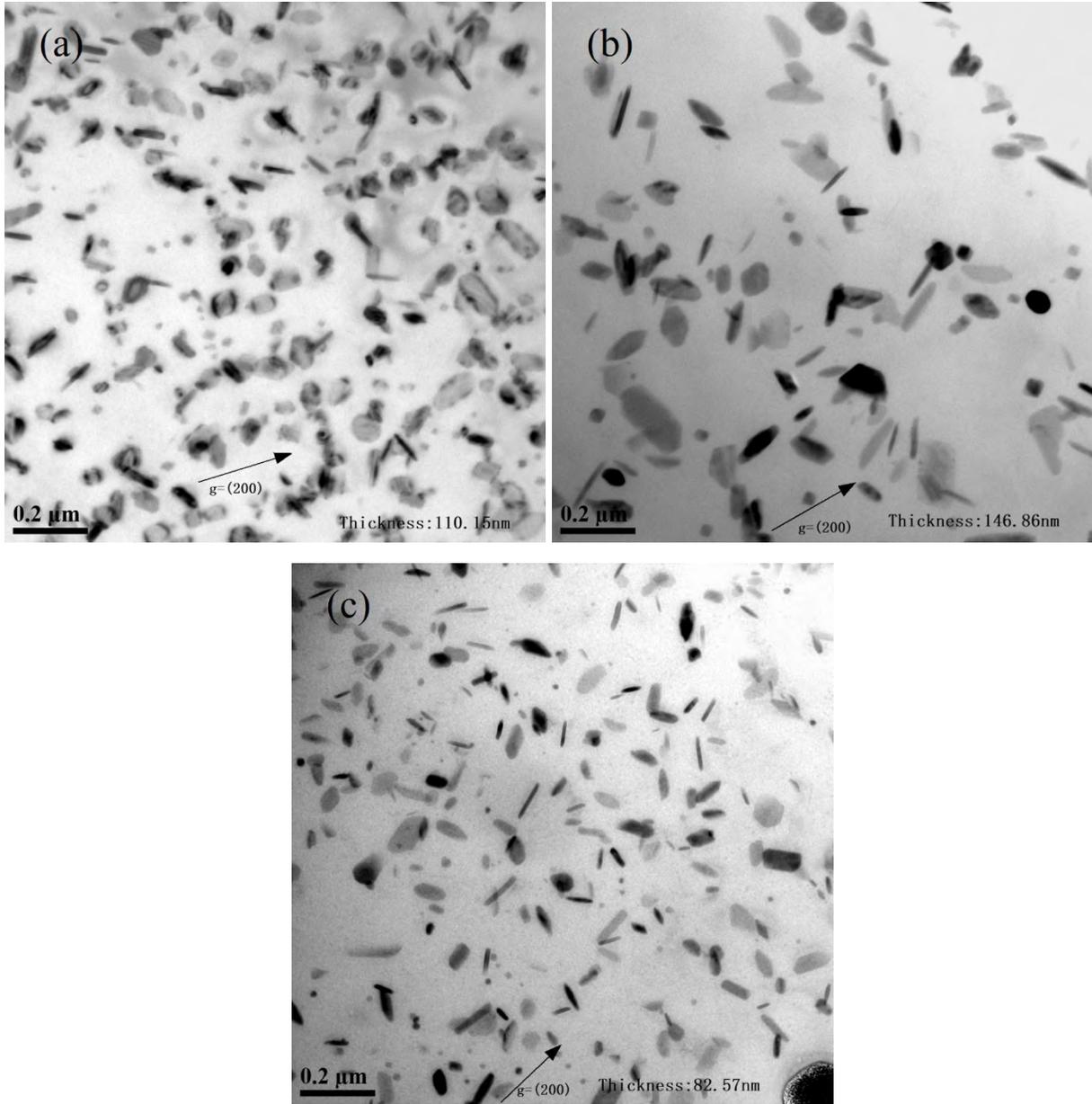


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205 **Fig. 4** Optical images showing the precipitation of dispersoids in the M1 alloy under different
206 heat treatment conditions, (a) 648K(375°C)/24h, (b) 448K(175°C)/5h + 648K(375°C)/24h and
207 (c) 523K(250°C)/12h + 648K(375°C)/24h.

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212 **Fig. 5** TEM bright field images showing the dispersoids in the M1 alloy after different heat
213 treatments, (a) 648K(375°C)/24h, (b) 448K(175°C)/5h + 648K(375°C)/24h and (c)
214 523K(250°C)/12h + 648K(375°C)/24h, recorded near the [001]_{Al} zone axis. The arrows indicate
215 the <100>_{Al} orientation.

216

217

Table 2 Dispersoid and DFZ parameters measured under different conditions

Alloy	Heat treatment	Area fraction of DFZ (%)	Equivalent diameter of dispersoids (nm)	Number density of dispersoids (μm^{-3})	Volume fraction of dispersoids (%)
Base	648K(375°C)/24h	79	97	72	0.32
Base	648K(375°C)/24h	51.4	80	-	0.82
M1 Alloy	648K(375°C)/24h	26.4	50	1055	2.69
M1 Alloy	448K(175°C)/5h + 648K(375°C)/24h	30	56	563	1.93
M1 Alloy	523K(250°C)/12h + 648K(375°C)/24h	23	42	1326	2.15
Deformed M1 Alloy	648K(375°C)/24h	7	68	294	2.58

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220 3.3 Precipitation of α -Al(MnFe)Si dispersoids in the deformed M1 alloy

221 The optical microstructure of the deformed M1 sample after the heat treatment at
 222 648K(375°C)/24h is shown in Fig. 6. At first glance, it appears that the dispersoids appeared
 223 almost everywhere, and their distribution was more uniform than that of the non-formed M1
 224 alloy (Fig. 4a). Furthermore, hardly any DFZs were observed in the deformed samples. The
 225 image analysis results show that the area fraction of DFZ in the deformed samples was only
 226 7.0%, while it was 26.5% in the non-formed M1 alloy (Table 2). This implies that the
 227 deformation has a strong benefit on the uniformity of the dispersoid distribution, particularly in
 228 the interdendrite regions.

229 A close observation revealed that the distribution of dispersoids was not uniform in the
 230 matrix, and some areas had a higher density than others. To better assess the number density and
 231 volume fraction of dispersoids in the deformed sample, the dispersoid zone was further divided
 232 to the dense dispersoid zone and the less dense dispersoid zone, as shown in Fig. 6. The former is
 233 mostly in the core of the aluminum grain and the latter is found toward the interdendrite region
 234 and close to Mn-containing intermetallic particles. TEM observation confirmed the existence of
 235 the two different zones and Fig. 7 shows TEM images of the different densities of the α -

236 Al(MnFe)Si dispersoids in these two zones. To quantify the number density and volume fraction
237 of the dispersoids, the following equations were used in the image analysis on TEM images:

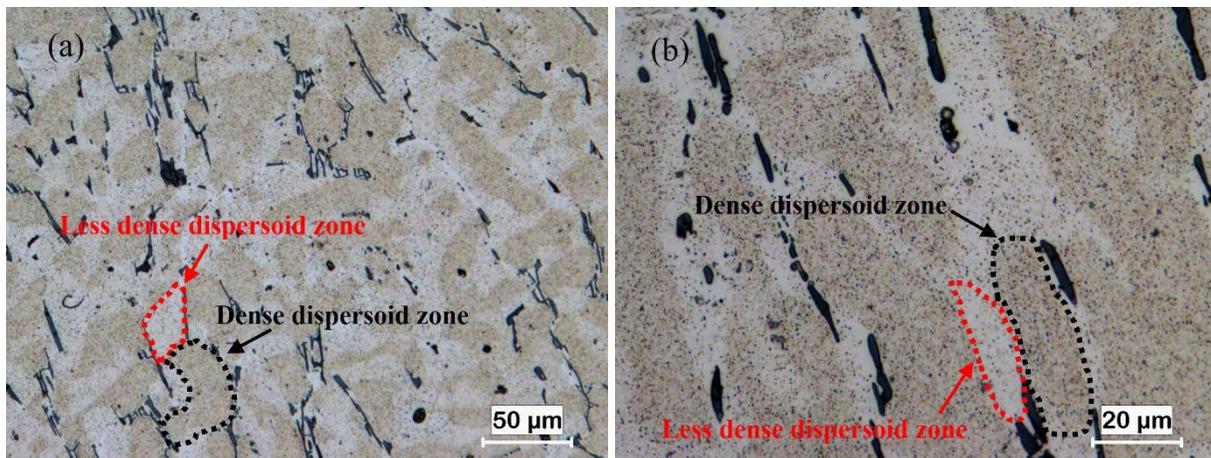
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$$N_{av} = N_d \cdot V_d + N_l \cdot V_l \quad (2)$$

239
$$V_d = V_{dd} \cdot V_d + V_{dl} \cdot V_l \quad (3)$$

240 Where N_{av} is the average number density. N_d and N_l are the number density of dispersoids in the
241 dense dispersoid zone and less dense dispersoid zone, respectively. N_d and N_l were measured by
242 image analysis based on TEM images, which were taken in the zones with high number density
243 of dispersoids and low number density of dispersoids, respectively. V_d and V_l are the volume
244 fractions of the dense dispersoid zone and less dense dispersoid zone, respectively. V_d and V_l
245 were measured by image analysis on the optical images of etched samples. V_{dd} and V_{dl} are the
246 volume fractions of dispersoids in the dense dispersoid zone and less dense dispersoid zone,
247 respectively, which were calculated according to Eq. 1.

248 The results are listed in Table 2. It can be seen that the dispersoid size is larger and the
249 number density is smaller than it is in the non-deformed sample under the same heat treatment
250 condition. However, the dispersoid volume fraction in the deformed sample is almost the same as
251 that in the non-deformed sample. It was reported that dislocations may enhance the precipitation
252 kinetics of second phase precipitation [21-26]. The effect of deformation and thus the generated
253 dislocations on the dispersoid precipitation will be discussed later.

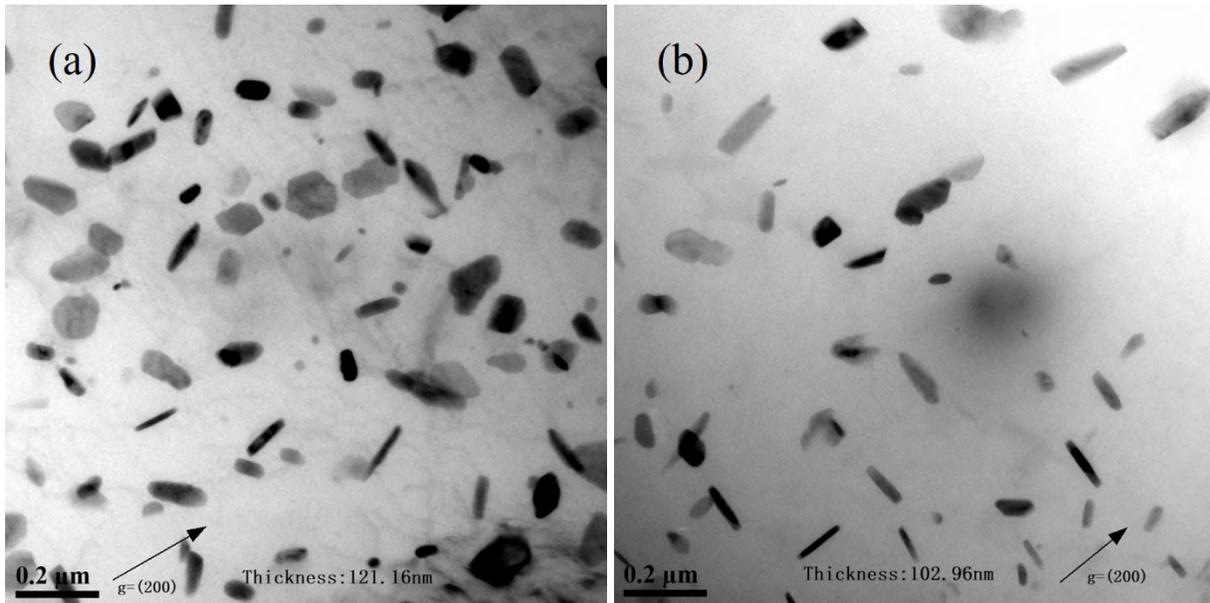
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257 **Fig. 6** Optical image showing the precipitation of dispersoids in the deformed M1 alloy after heat
258 treatment at 648K(375°C)/24h: (a) the dense dispersoid zone and the less dense dispersoid zone
259 and (b) enlarged image of (a).



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263 **Fig. 7** TEM bright field images showing the dispersoids in the deformed M1 alloy (0.2 strain +
 264 648K(375°C)/24h), a) in the dense dispersoid zone and b) in the less dense dispersoid zone.

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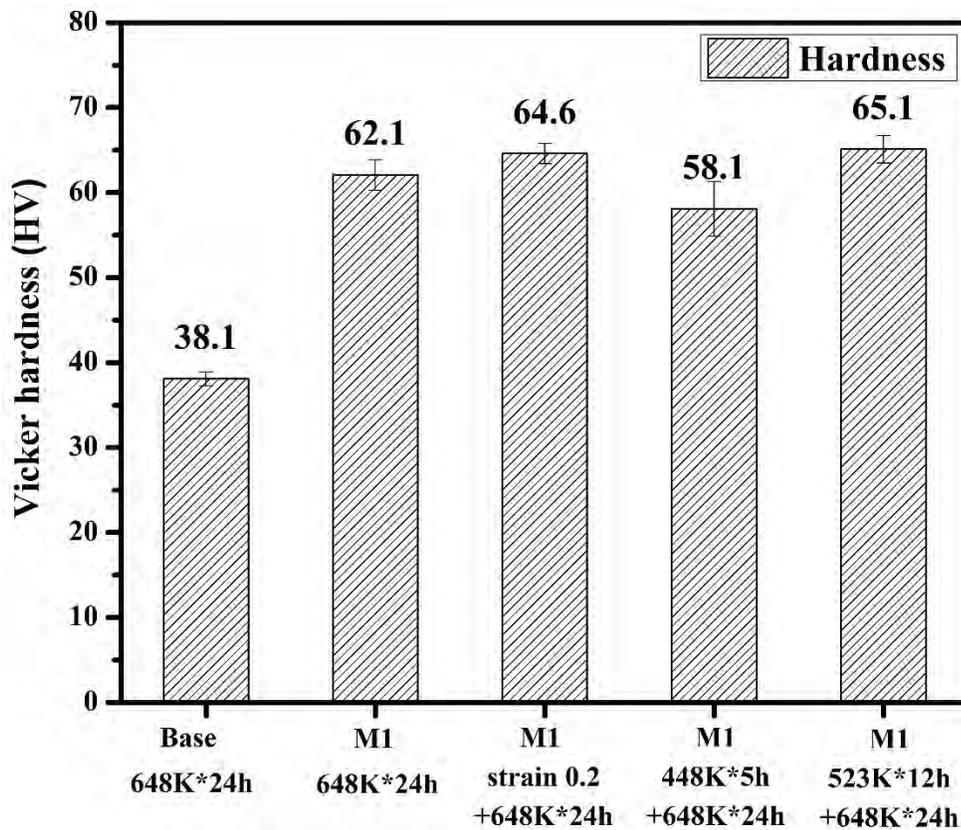
266 3.4 The effect of Mg and deformation on microhardness

267 To confirm the dispersoid precipitation and its strengthening effect, the Vicker
 268 microhardness of the base and M1 alloys under different conditions was measured. The results of
 269 hardness measurements for the base and M1 alloys are shown in Fig. 8. Compared to the base
 270 alloy, the hardness values of the Mg containing M1 alloy under all heat treatment conditions are
 271 remarkably higher. Those hardness increases include the Mg solid solution strengthening and the
 272 dispersoid strengthening. Because no Mg-containing phase is formed after the final heat
 273 treatment at 648 K (375°C) (Figs. 5 and 7), most of Mg solute atoms remain in the aluminum
 274 matrix of the M1 alloy. It is reported in our previous work [2] that 1% Mg in solid solution can
 275 increase 12-13 MPa of the yield strength in aluminum alloys. Using the relationship $YS \approx HV/3$
 276 [30], it represents approximately 4 HV hardness increment. It is apparent that the hardness
 277 increases of the Mg containing M1 alloy after the heat treatment is mainly due to the dispersoid
 278 strengthening. For example, at the same heat treatment condition (648K(375°C)/24h), the
 279 hardness of the Mg containing M1 alloy is 26 HV higher than that of the base alloy, indicating
 280 the strong dispersoid strengthening effect caused by adding Mg.

281 The hardness of the sample after the 523K(250°C)/12h + 648K(375°C)/24h two-step
 282 treatment is 65 HV while it is 58 HV for the sample that experienced the 448K(175°C)/5h +
 283 648K(375°C)/24h two-step treatment, suggesting that the two-step treatment at 523K(250°C)/12h
 284 + 648K(375°C)/24h is more effective at enabling the dispersoid strengthening effect, which was
 285 confirmed by the optical and TEM observations (Figs. 4 and 5).

286 The hardness of the deformed sample (0.2 strain compression) is moderately higher than
 287 that of the non-deformed M1 sample under the same heat treatment condition. It is worth to
 288 mention that the work hardening by the 0.2 strain compression deformation is almost negligible
 289 after the heat treatment at 648 K (375°C). The deformed sample's hardness is similar to the
 290 sample after the 523K(250°C)/12h + 648K(375°C)/24h two-step treatment. Therefore, the best
 291 strengths of materials are achieved by the two-step 523K(250°C)/12h + 648K(375°C)/24h
 292 treatment and by the deformation.

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296 **Fig. 8** Microhardness of the base alloy and M1 alloy under various experimental conditions.

297

298 3.5 Metastable Mg₂Si-based nucleation mechanism

299 According to above observation, the number density and the volume fraction of α -
300 Al(MnFe)Si dispersoids in the M1 alloy (1%Mg) are much higher than those in the base alloy
301 without Mg. It should be noted that α -Al(MnFe)Si dispersoids do not contain Mg, which means
302 that Mg is not a necessary component of the α -Al(MnFe)Si phase. The only possible phase
303 containing Mg in the M1 alloy is the metastable Mg₂Si precipitates that appeared during heating
304 process. To explore how Mg and metastable Mg₂Si promote the dispersoid formation, the
305 precipitation process in the M1 alloy during heat treatment was investigated using the quenching
306 technique described in Fig. 1a and TEM analysis.

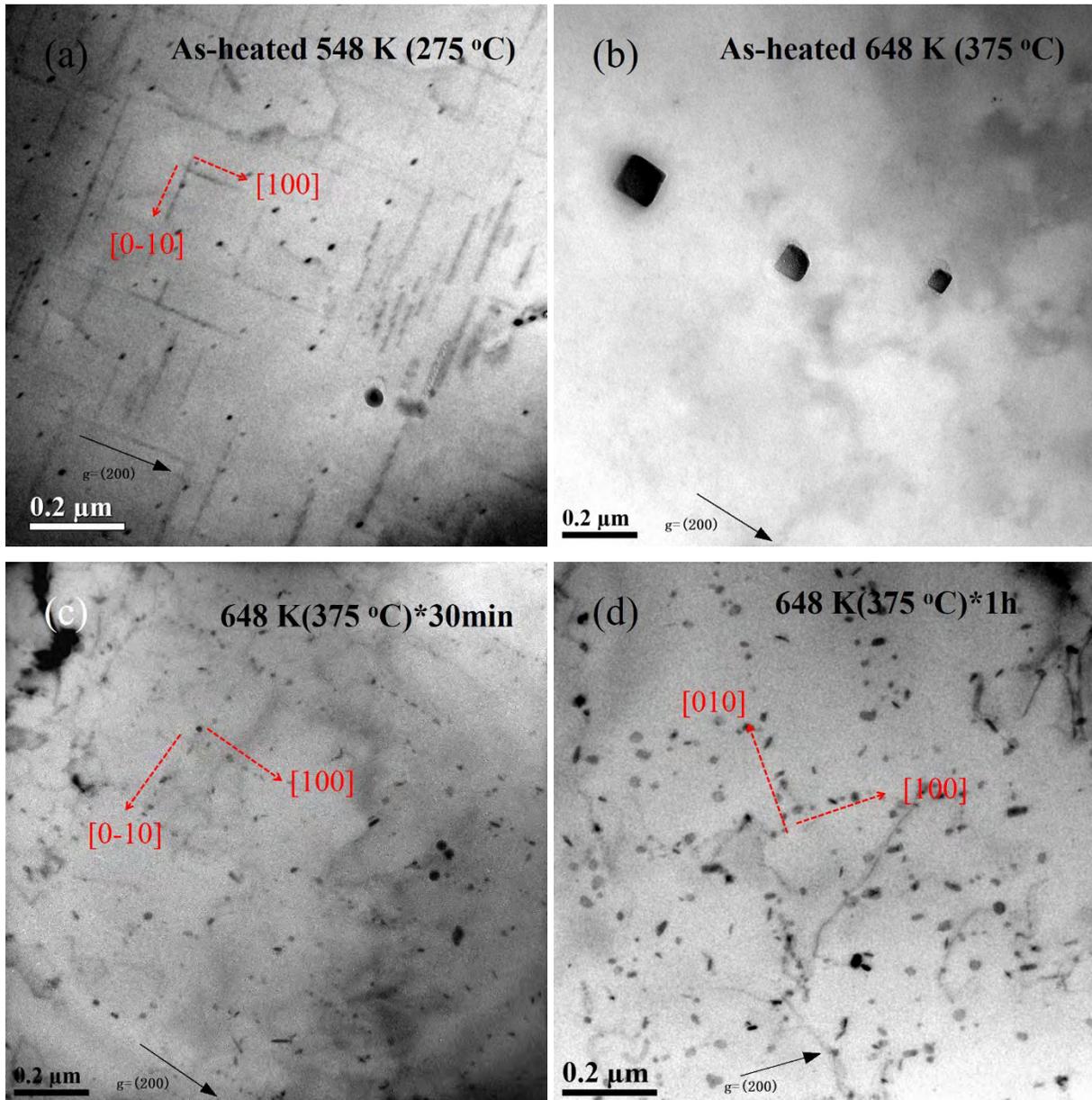
307 Fig. 9 shows TEM images of the precipitation of the metastable Mg₂Si precipitates and α -
308 Al(MnFe)Si dispersoids during different stages of the heat treatment. When the samples were
309 heated to 548 K (275 °C), a number of lath-like precipitates appeared (Fig. 9a), which were
310 identified to be β' -Mg₂Si based on the morphology and orientation of the precipitates [9-12] and
311 the corresponding selected area diffraction pattern (SADP, Fig. 9f) [31]. The small black dots are
312 the cross sections of the lath-like precipitates. These lath-like precipitates growing along $\langle 100 \rangle_{Al}$
313 are approximately 10 nm in width and 100-200 nm in length. It is evident that the supersaturated
314 solid solution after solidification in the M1 alloy was decomposed during the heating to 548 K
315 (275 °C) and the β' -Mg₂Si precipitated. It should be mentioned that no α -Al(MnFe)Si dispersoids
316 formed at this stage.

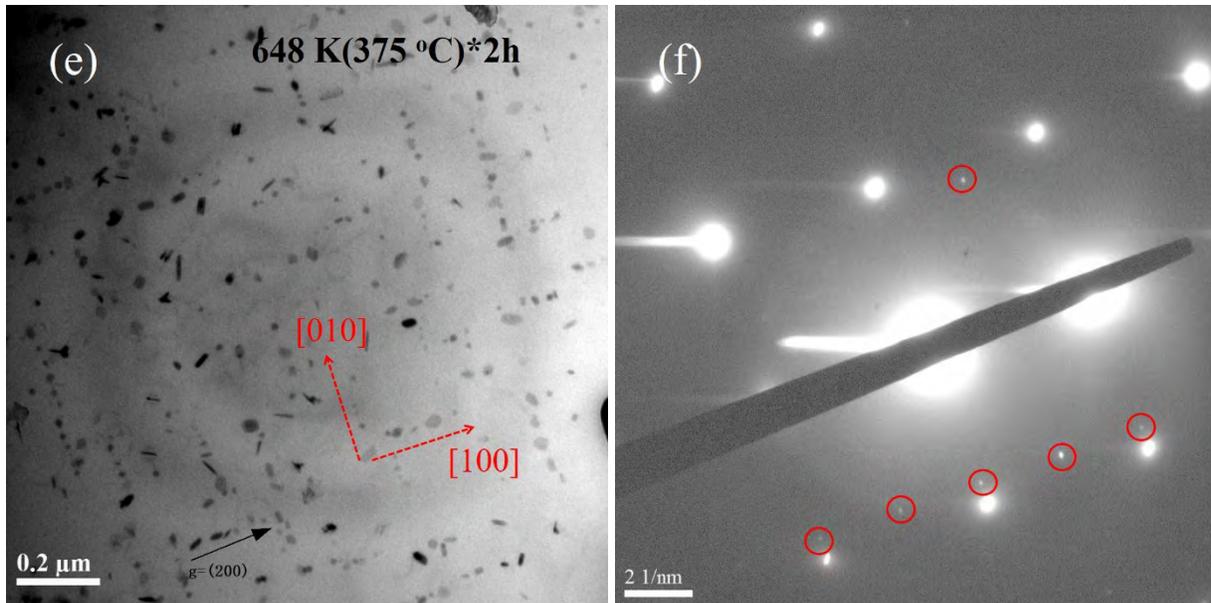
317 After the samples heated to 648 K (375 °C), all lath-like β' -Mg₂Si dissolved and left only a
318 few of the cubic-like equilibrium Mg₂Si particles (Fig. 9b). No visible α -Al(MnFe)Si dispersoids
319 were observed. During isothermal holding at 648 K (375 °C), fine α -Al(MnFe)Si dispersoids
320 appeared, and after 30 mins the size of dispersoids was approximately 10-20 nm (Fig. 9c). The
321 dispersoids were distributed along $\langle 001 \rangle_{Al}$ direction which is the preferred precipitation
322 orientation of previous β' -Mg₂Si.

323 After holding for 1 and 2 hours at 648 K (375 °C), the dispersoids gradually grew, as
324 shown in Figs. 9d and e. The precipitation direction of dispersoids along $\langle 001 \rangle_{Al}$ is still clearly
325 visible, which means that most dispersoids nucleated and grew on the previous β' -Mg₂Si sites,
326 even though they dissolved. As the holding time prolonged towards 24 hours, Ostwald ripening
327 (coarsening) occurred and the size of dispersoids after 24 h reached 50 nm, as shown in Fig. 6a
328 and Table 2. Due to a great number of dispersoids, the preferred precipitation direction of the

329 dispersoids seems to be a little unclear. However, a majority of the dispersoids can still be seen
330 distributed along $\langle 001 \rangle_{Al}$ direction. Certainly, after the initial nucleation and growth, the
331 dispersoids might have chances to nucleate and grow on other sites, such as at dislocations. After
332 being heat-treated for 24 h, it is not necessary that all the dispersoids were along $\langle 001 \rangle_{Al}$
333 direction. It is also worth mentioning that the nucleation of the dispersoids on equilibrium β -
334 Mg_2Si was not observed.

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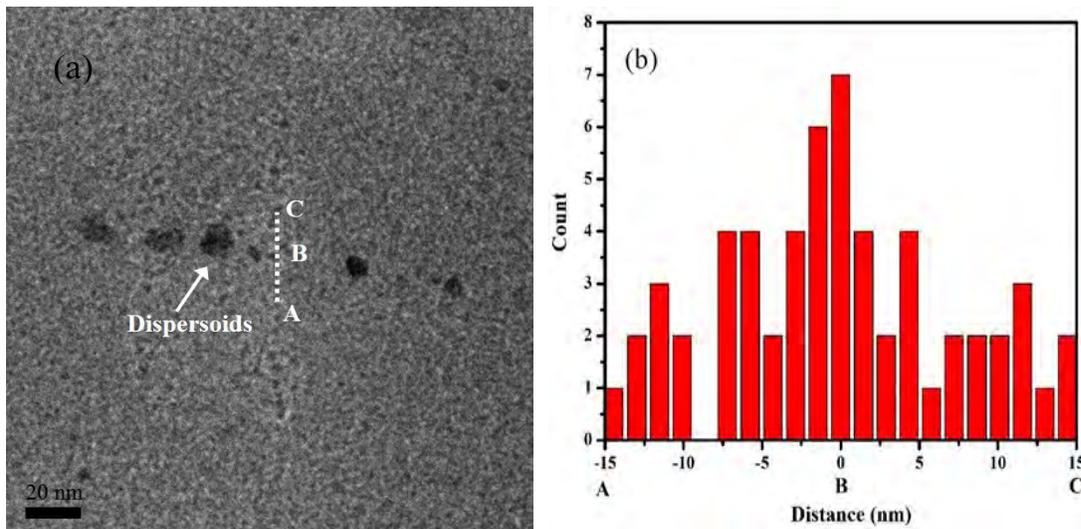
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340 **Fig. 9** The precipitation process in the M1 alloy (a) as-heated at 548 K (275 °C), (b) as-heated at
 341 648 K (375 °C), (c) 648 K (375 °C) for 30 min, (d) 648 K (375 °C) for 1 h, (e) 648 K (375 °C) for
 342 2 h, (f) the selected area diffraction pattern (SADP) corresponding to the image (a) and the
 343 typical diffraction spots of β' -Mg₂Si indicated by the red circles.

344

345 The local chemical composition at the sites of dissolved β' -Mg₂Si was analyzed using TEM-
 346 EDS line scanning. The typical result of the Si distribution along the dissolved β' -Mg₂Si in the
 347 sample held for 15 minutes at 648 K (375 °C) are shown in Figure 10. It can be seen that a few
 348 small α -Al(MnFe)Si particles began to precipitate along $\langle 001 \rangle_{Al}$ direction (see Fig. 10a), which
 349 was a previous site of β' -Mg₂Si. Across this site (the scan line A-C), the Si concentration at the
 350 location of the dissolved β' -Mg₂Si was higher than in the surrounding aluminum matrix (local Si
 351 enrichment), as shown in Fig. 10b. As mentioned above, Mg is not a necessary element but Si is
 352 the essential element for α -Al(MnFe)Si dispersoid formation. Without Si, α -Al(MnFe)Si
 353 dispersoids can hardly form in the matrix. It becomes evident that α -Al(MnFe)Si would
 354 preferentially nucleate on the sites of previous β' -Mg₂Si precipitates, which could provide more
 355 Si atoms than at other places in the aluminum matrix. It should be noted that the intermediate
 356 phase, the u-phase, that could promote the nucleation of α -Al(MnFe)Si reported in [18], has not
 357 been observed in the present study, which could be due to the different alloy compositions and
 358 heat treatment conditions.



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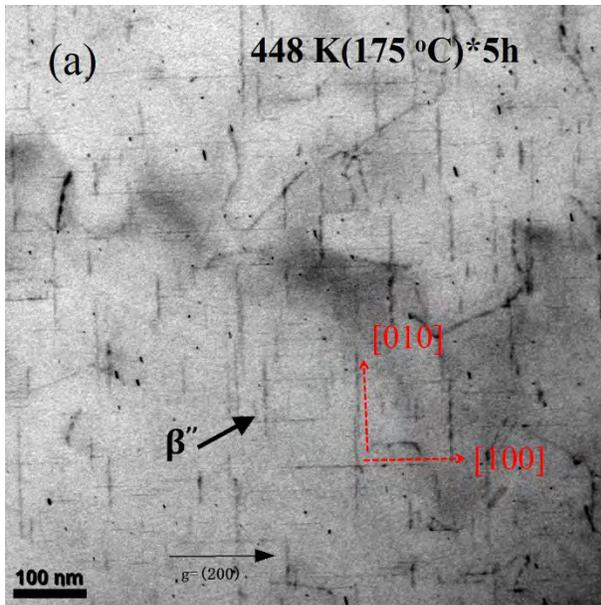
362 **Fig. 10** TEM analysis of the M1 sample held at 648 K (375 °C) for 15 minutes showing the local
 363 Si enrichment on the sites of previous β' -Mg₂Si precipitates, (a) TEM image on the site of a
 364 previous β' -Mg₂Si and the position of the line scanning (A-C) and (b) Si distribution along the
 365 line A-C.

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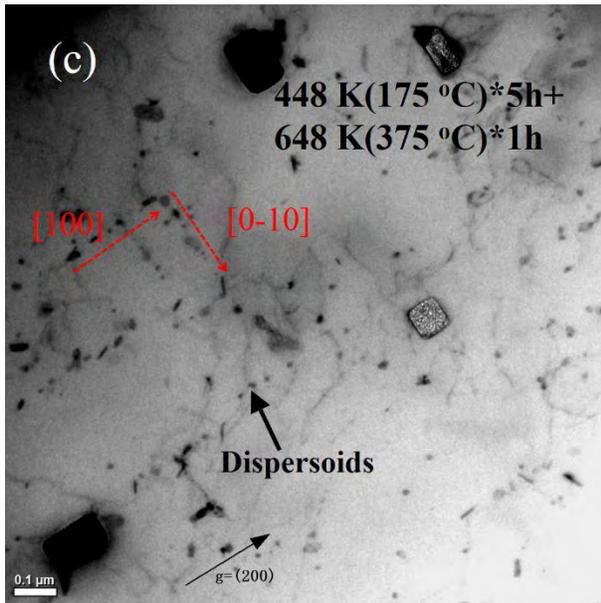
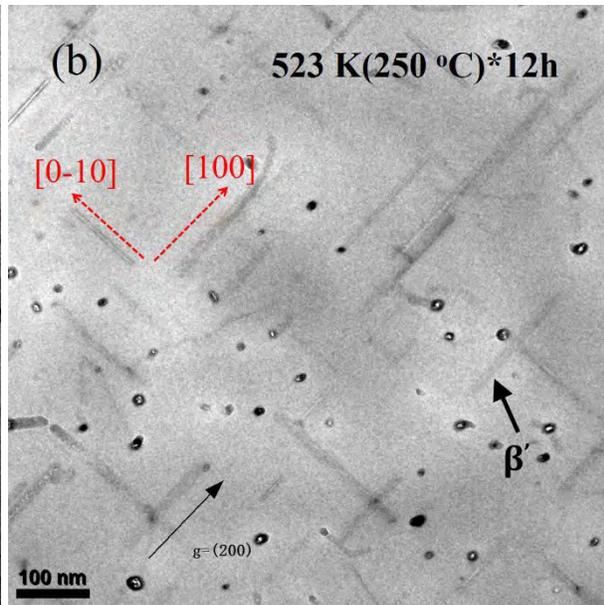
367 To further distinguish the effect of the pre-existing β'' -Mg₂Si and β' -Mg₂Si on the
 368 dispersoid formation, the two-step heat treatments with the first step at 448K(175°C)/5h and at
 369 523K(250°C)/12h for controllable β'' -Mg₂Si and β' -Mg₂Si were conducted. In the section 3.2,
 370 the effect of these two-step heat treatments on the precipitation of α -Al(MnFe)Si dispersoids
 371 were described and compared. The details of the precipitation process under these two conditions
 372 are shown in Fig. 11. For the sample treated at 448 K (175 °C) for 5 h, the only phase that
 373 appeared was the needle-like β'' -Mg₂Si located along the $\langle 001 \rangle_{Al}$ direction (Fig. 11a), identified
 374 based on the morphology and orientation of the precipitates and the corresponding selected area
 375 diffraction pattern (SADP, Fig. 11e) [32]. The needle-like β'' -Mg₂Si precipitates were
 376 approximately 3 nm in width and 20-100 nm in length. During further heating to 648 K (375 °C),
 377 all needle-like β'' -Mg₂Si dissolved in the aluminum matrix. For the sample treated at 523 K (250
 378 °C for 12 h), the precipitated phase was lath-like β' -Mg₂Si with a size of approximately 10 nm in
 379 width and 100-200 nm in length (Fig. 11b), which also dissolved in aluminum matrix during
 380 further heating to 648 K (375 °C). The β' -Mg₂Si was identified based on the corresponding

381 SADP (Fig. 11f) [31]. After holding for 1 h at 648 K (375 °C) in both 448K(175°C)/5h and
382 523K(250°C)/12h samples, all of the α -Al(MnFe)Si dispersoids lay along $\langle 001 \rangle_{Al}$ direction
383 (Figs. 11c and d), which indicates that the α -Al(MnFe)Si dispersoids nucleated and grew in the
384 sites of previous β'' -Mg₂Si or β' -Mg₂Si precipitates. Although the β'' -Mg₂Si precipitates in the
385 448K(175°C)/5h sample are denser than the β' -Mg₂Si precipitates in the 523K(250°C)/12h
386 sample, the amount of α -Al(MnFe)Si dispersoids in the 448K(175°C)/5h + 648K(375°C)/1h
387 sample (Fig. 11c) is much lower than that in the 523K(250°C)/12h + 648K(375°C)/1h sample
388 (Fig. 11d). Compared to the one step heat treatment sample (648K(375°C)/1h, Fig. 9d), the
389 amount of α -Al(MnFe)Si dispersoids in the 448K(175°C)/5h + 648K(375 °C)/1h sample is also
390 lower. In addition, the number density and volume fraction of the dispersoids in the final treated
391 sample (448K(175°C)/5h + 648K(375°C)/24h) are lower than that in the 523K(250°C)/12h +
392 648K(375°C)/24h final sample (Table 2). Here, it has to remind that the number density and
393 volume fraction of the dispersoids in the M1 sample after 448K(175°C)/5h + 648K(375°C)/24h
394 treatment is still higher than that in the base alloy without any pre-existing Mg₂Si, showing a
395 positive effect in promoting the dispersoid formation. It is apparent that pre-existing β' -Mg₂Si
396 precipitates are more effective at promoting dispersoid nucleation than pre-existing β'' -Mg₂Si
397 precipitates. It is most likely that the local Si enrichment of dissolved β' -Mg₂Si is larger than that
398 of the β'' -Mg₂Si precipitates, because of the large size of β' -Mg₂Si. This, in turn, creates a more
399 favorable condition for α -Al(MnFe)Si dispersoid nucleation and growth. During the heating
400 process towards higher temperature (648 K (375 °C)), most of β'' - and β' -Mg₂Si dissolved in the
401 aluminum matrix and it left very few equilibrium β -Mg₂Si particles (Fig. 11c). When the
402 precipitation of dispersoids started, it was not observed that the dispersoids nucleated on
403 equilibrium β -Mg₂Si particles.

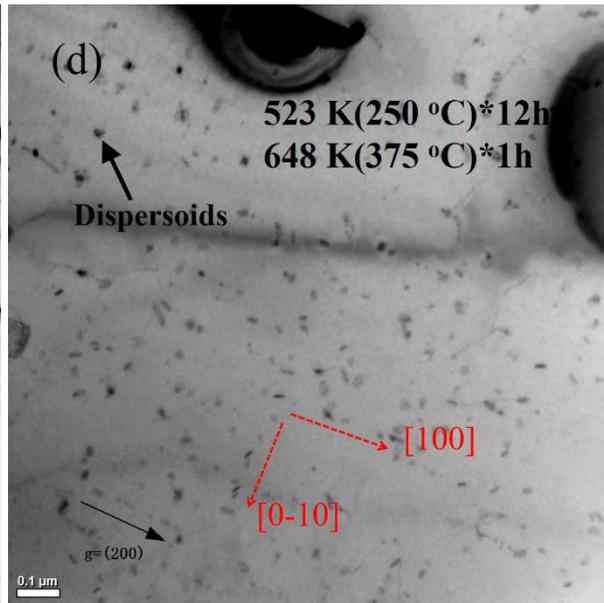
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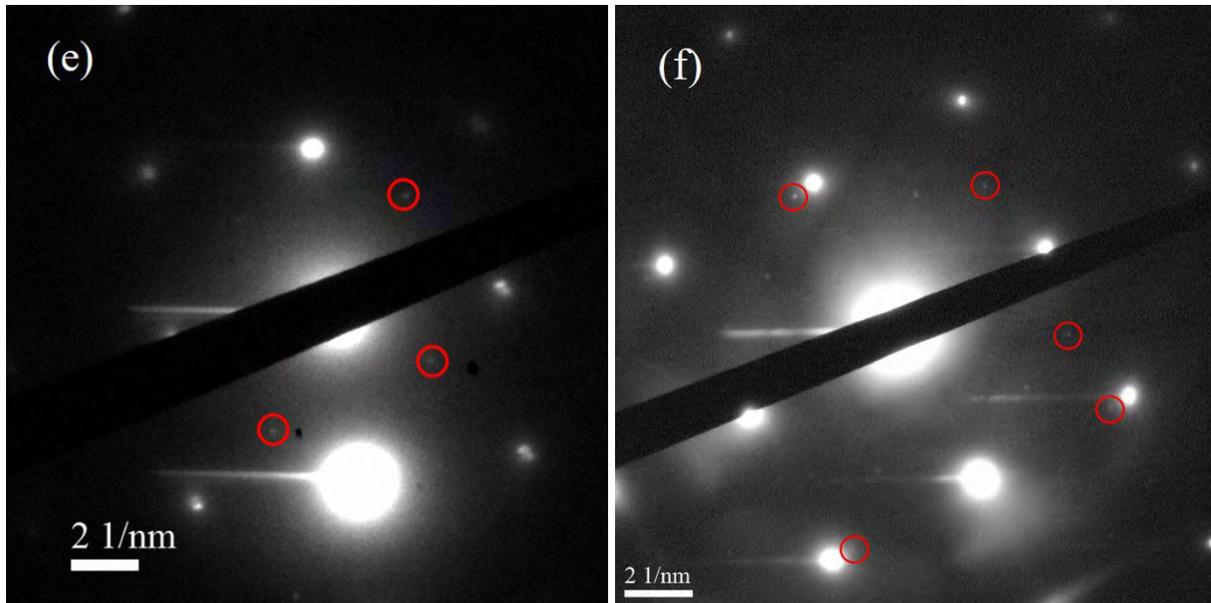


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409 **Fig. 11** TEM images of the M1 samples experienced (a) 448 K (175 °C) for 5 h, (b) 523 K (250
 410 °C) for 12 h, (c) 448 K (175 °C) for 5 h + 648 K (375 °C) for 1 h, (d) 523 K (250 °C) for 12 h +
 411 648 K (375 °C) for 1 h, (e) the selected area diffraction pattern (SADP) corresponding to the
 412 image (a) and the typical diffraction spots of β'' -Mg₂Si indicated by the red circles, (f) the
 413 selected area diffraction pattern (SADP) corresponding to the image (b) and the typical
 414 diffraction spots of β'' -Mg₂Si indicated by the red circles.

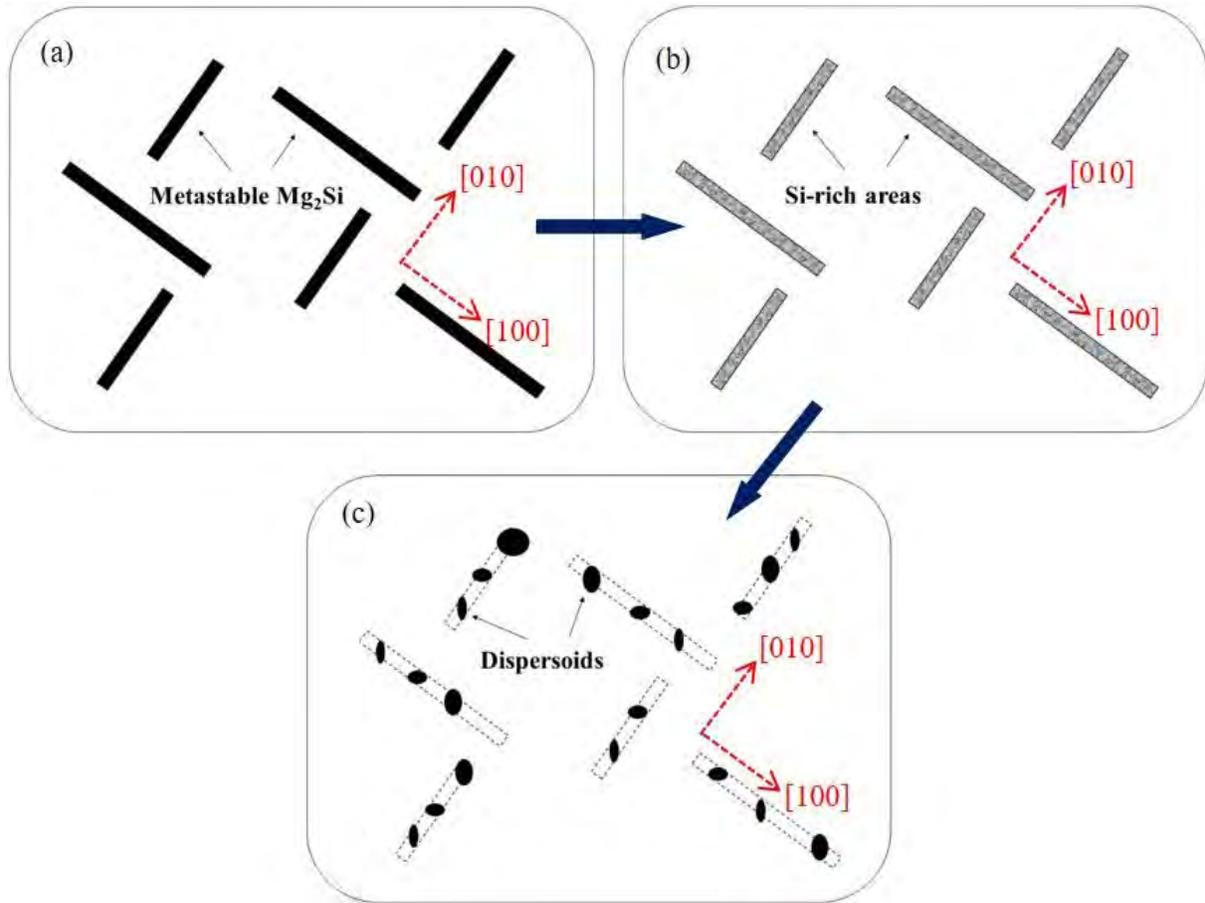
415

416 Based on the above results, the nucleation mechanism of the dispersoids based on the
 417 metastable Mg₂Si precipitates can be described as follows (Fig. 12). In the Mg containing M1
 418 samples under various heat treatments (including both one step and two-step treatments), a large
 419 number of metastable Mg₂Si phase first precipitated during heating process at the temperature
 420 range of 423-548 K (150-275 °C) (Fig. 12a), and then gradually dissolved at higher temperatures
 421 of 573-648 K (300-375 °C) (Fig. 12b). The sites of the dissolved metastable Mg₂Si were still Si-
 422 rich, which provided favorable sites for the nucleation of α -Al(MnFe)Si dispersoids. When the
 423 samples reach the formation temperature of α -Al(MnFe)Si, for example above 573-648 K (350-
 424 375 °C), α -Al(MnFe)Si dispersoids started to nucleate and grow along the $\langle 001 \rangle_{Al}$ direction in
 425 the Si-rich sites of the previously metastable Mg₂Si (Fig. 12c). During heating process, two
 426 possible metastable phases could be formed under different heating rates, namely, β'' -Mg₂Si and
 427 β' -Mg₂Si. The results obtained in the present work indicated that pre-existing β' -Mg₂Si

428 precipitates were more effective in the promotion of the dispersoid nucleation than pre-existing
429 β'' -Mg₂Si. This probably implies that the size of the lath-like β' -Mg₂Si precipitates was larger
430 than that of needle-like β'' -Mg₂Si, and thus the available Si on Si-rich sites of the former was
431 higher than that of the latter, resulting in a more favorable condition for dispersoid nucleation
432 and growth.

433 It is understandable that in the Mg-free base alloy, no pre-existing metastable Mg₂Si could be
434 formed during the heating process. Thus, the precipitation of α -Al(MnFe)Si dispersoids was so
435 difficult that only an insufficient number of dispersoids formed even after extensively prolonged
436 heat treatment (648K(375°C)/72h). It is obvious that Mg element is crucial for the precipitation
437 of α -Al(MnFe)Si dispersoids because Mg promotes the formation of uniformly distributed Mg₂Si
438 precipitates, which provide the nucleation sites for the α -Al(MnFe)Si dispersoids when Mg₂Si
439 precipitates were dissolved during heat treatment. In previous works [17, 18], the pre-existing β' -
440 Mg₂Si was reported to be the prerequisite for a high density nucleation of α -Al(MnFe)Si
441 dispersoids in Mn containing Al-Mg-Si alloys, which is confirmed by the present work in the Al-
442 Mn-Mg 3xxx alloy.

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Fig. 12 Schematic diagram of the dispersoid formation based on metastable Mg₂Si nucleation mechanism, (a) metastable Mg₂Si precipitated, (b) Mg₂Si dissolved forming Si-rich areas and (c) α -Al(MnFe)Si dispersoid nucleation and growth in the Si-rich sites of previous metastable Mg₂Si along the $\langle 001 \rangle_{Al}$ direction.

451 3.6 Dislocation-based nucleation mechanism

452 As described in Section 3.3, the cold deformation of the M1 sample that generated a great
 453 number of dislocations had an important influence on the dispersoid precipitation. {111} planes
 454 are the close-packed planes of aluminum and they are also the main dislocation slip planes.
 455 Hence, TEM bright field images were taken on the (-111) plane near the [011] zone axis to
 456 observe the dislocations and the precipitation process (see Fig. 13). After the deformed sample
 457 was heated to 548 K (275 °C), both β' -Mg₂Si and dislocations can be observed as shown in Fig.
 458 13a and b. When the deformed M1 sample held at 648 K (375 °C) for 1 h, dispersoids and
 459 dislocations coexisted in aluminum matrix, but the β' -Mg₂Si disappeared and dissolved (Fig.

460 13c). Here, most of the dispersoids precipitated on dislocations, markedly different from the
461 precipitation seen in the non-deformed sample (Fig. 9a).

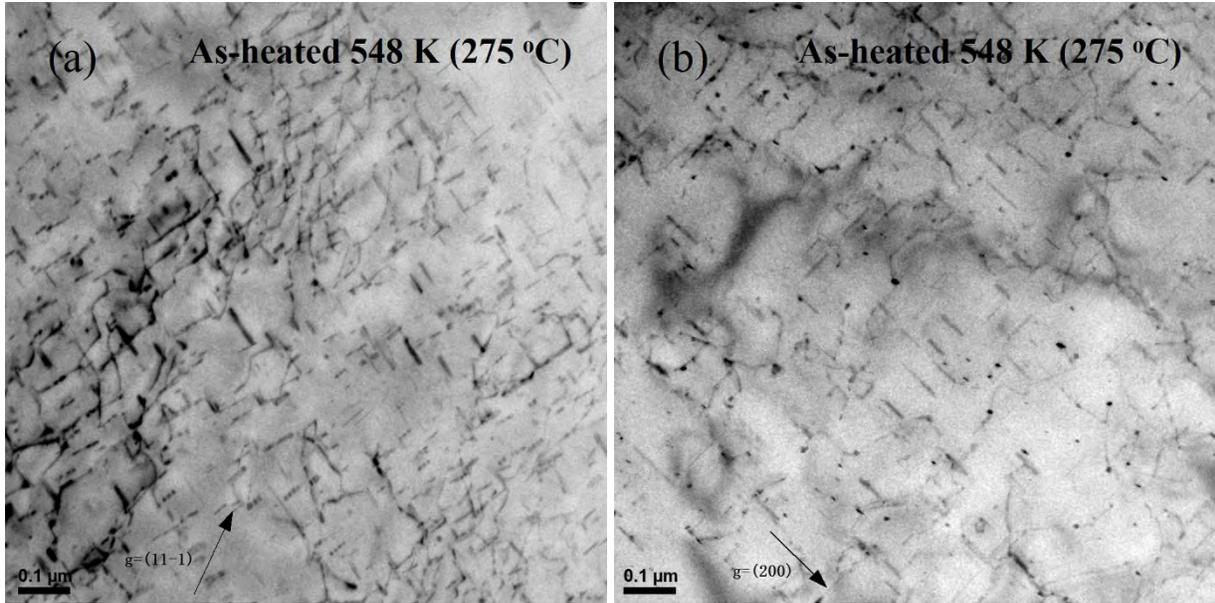
462 To verify the orientation relationship between the α -Al(MnFe)Si dispersoids and the β' -
463 Mg₂Si precipitates, the microstructure of the deformed samples was observed with the (200)
464 crystal plane near the [001] direction. Growing along the $\langle 001 \rangle_{\text{Al}}$ direction, lath-like β' -Mg₂Si
465 precipitates were clearly seen without any interference from the dislocations in the sample heated
466 to 548 K (275 °C) (Fig. 13b). The sample held at 648 K (375 °C) for 1 h showed that β' -Mg₂Si
467 had already dissolved but that α -Al(MnFe)Si dispersoids did not lie along the $\langle 001 \rangle_{\text{Al}}$ direction,
468 but rather along the dislocations (Figs. 13c and d). This finding indicates that the sites of the
469 previous β' -Mg₂Si precipitates were no longer the priority locations for dispersoids nucleation in
470 the deformed sample. Due to the presence of a great number of dislocations, the fast diffusion of
471 the alloying elements (including Si) would weaken the advantage of the local Si enrichment from
472 the dissolved β' -Mg₂Si for α -Al(MnFe)Si dispersoid nucleation. Instead of the sites of previous
473 β' -Mg₂Si, dislocations become the predominate sites for the dispersoid nucleation in the
474 deformed sample.

475 When the deformed sample was held for 24 hours at 648 K (375 °C), the dispersoids kept
476 growing and became coarse (Fig. 13e). The size of dispersoids in the deformed sample after
477 heating at 648 K (375 °C) for 24 h was larger than that in the non-deformed sample, whereas the
478 number density of dispersoids in the former is less than that in the latter (Table 2). It is likely that
479 the fast diffusion of alloying elements through the dislocations can benefit the Ostwald ripening
480 of dispersoids (coarsening). However, the volume fraction of the dispersoids in the deformed
481 sample remains at a level similar to that found in the non-deformed sample.

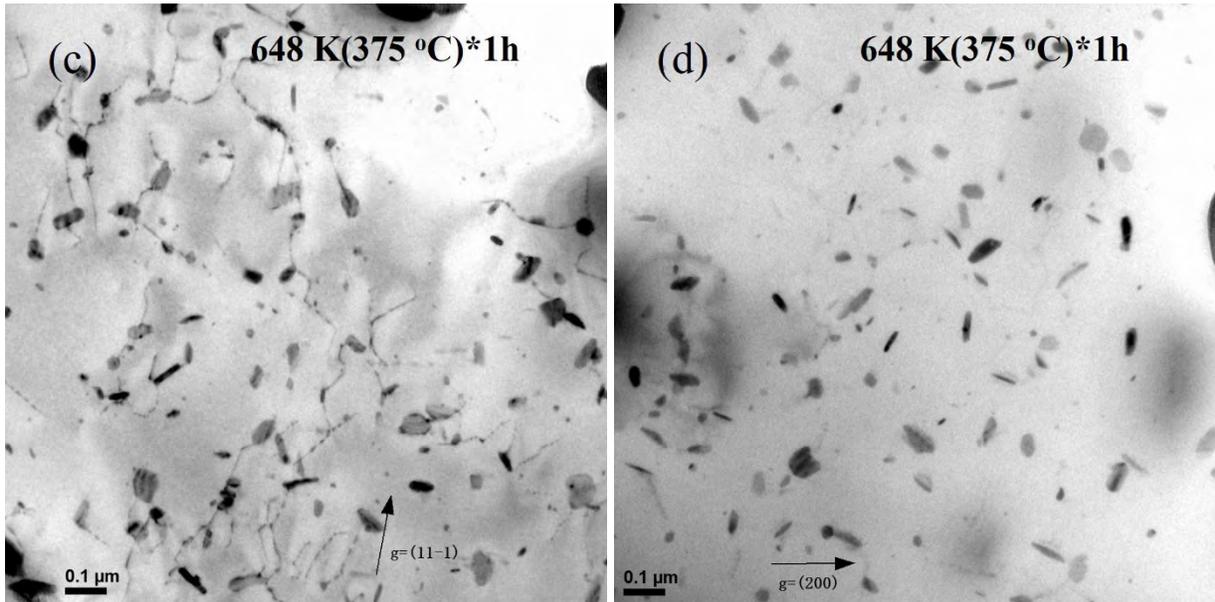
482 In the as-cast microstructure, there were Mn depletion zones close to the Al₆(Mn,Fe)
483 intermetallic particles and to the aluminum grain boundaries [33], causing the DFZs during heat
484 treatment because of the lack of the essential element Mn required for α -Al(MnFe)Si dispersoid
485 formation (Fig. 4). In the deformed sample, a great number density of dislocation piled up
486 around intermetallic particles and grain boundaries because the intermetallic particles and grain
487 boundaries were barriers to block dislocation migrations during deformation. During heat
488 treatment, these dislocations acted not only as fast diffusion channels to transport Mn solutes to
489 the Mn depletion zones but also as favorable nucleation sites, making the nucleation and growth
490 of α -Al(MnFe)Si dispersoids possible in those zones. This is why, besides the dense dispersoid

491 zones in the cores of the aluminum grains, there were the less dense dispersoid zones close to the
492 $\text{Al}_6(\text{Mn,Fe})$ intermetallic particles and grain boundaries in the deformed sample (Fig. 6), which
493 was the DFZ where the precipitation of $\alpha\text{-Al}(\text{MnFe})\text{Si}$ was impossible in the non-deformed
494 sample. This resulted in a large reduction of DFZs and a more uniform dispersoid distribution
495 when compared to the non-deformed sample.

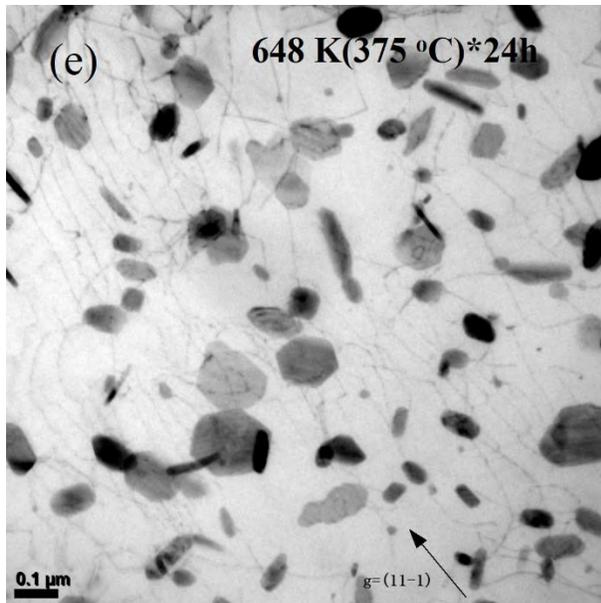
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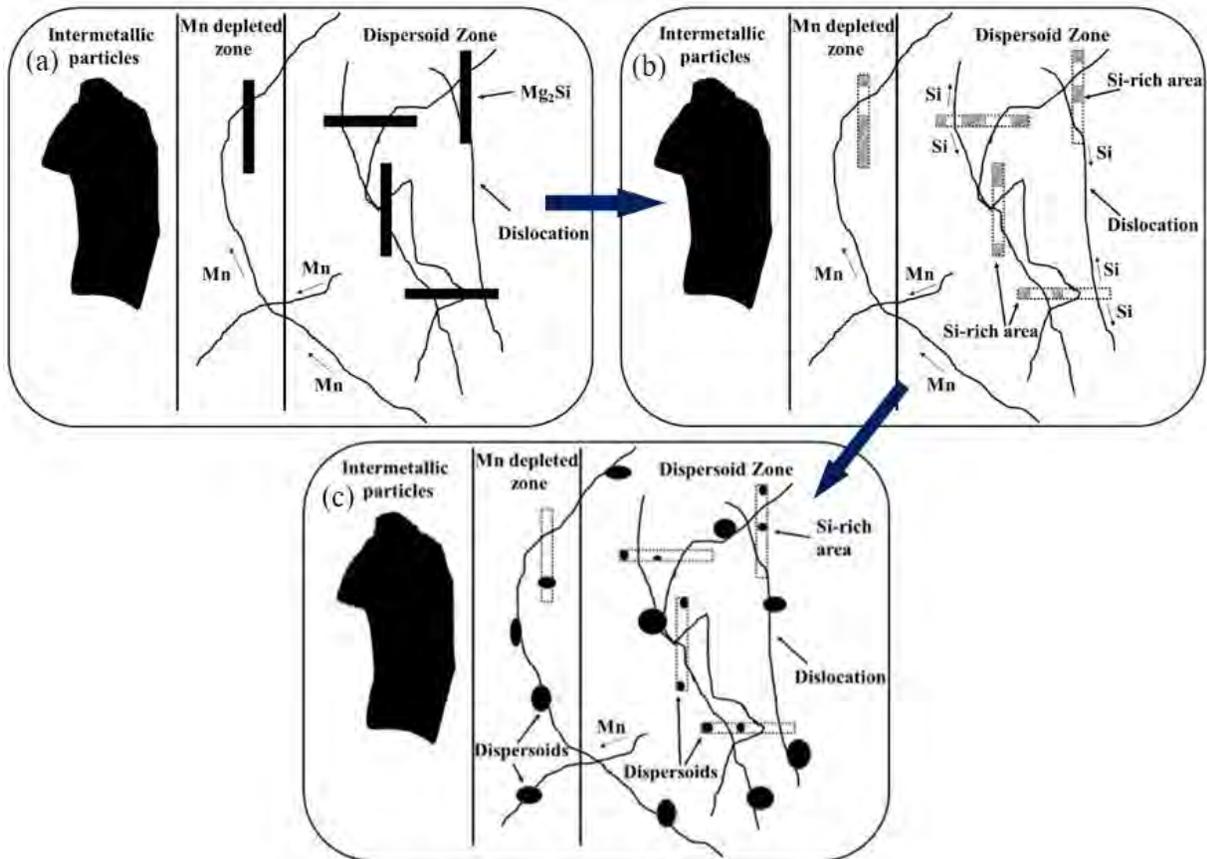
501 **Fig. 13** The precipitation process in the deformed M1 samples (a) heated to 548 K (275 °C)
 502 showing dislocations, recorded near $[011]_{Al}$; (b) heated to 548 K (275 °C) showing β' -Mg₂Si,
 503 recorded near $[001]_{Al}$; (c) held at 648 K (375 °C) for 1 h, recorded near $[011]_{Al}$, (d) held at 648 K
 504 (375 °C) for 1 h, recorded near $[001]_{Al}$; (e) held at 648 K (375 °C) for 24 h, recorded near
 505 $[011]_{Al}$.

506

507 Based on the above results, the nucleation mechanism of the dispersoids based on
 508 dislocations in the deformed sample can be schematically expressed as follows (Fig. 14). During
 509 the heating process toward 548 K (275 °C), metastable β' -Mg₂Si phase first precipitated out, and
 510 a great number of dislocations and β' -Mg₂Si co-existed in the microstructure (Fig. 14a). As the
 511 temperature continued to increase toward 648 K (375 °C), β' -Mg₂Si precipitates dissolved before
 512 the precipitation of α -Al(MnFe)Si dispersoids, and many dislocations remained in the aluminum
 513 matrix (Fig. 14b). Although the effect of local Si enrichment became weaker due to the fast
 514 diffusion of Si along dislocations, Si-rich areas would still exist in the aluminum matrix. When
 515 the temperature rose above the precipitation temperature of the dispersoids (thermal holding at
 516 648 k (375 °C)), α -Al(MnFe)Si dispersoids began to nucleate and grow on the dislocations and
 517 Si-rich areas (Fig. 14c). Generally, the size of the dispersoids nucleated on dislocations was
 518 larger than that on Si-rich areas due to the fast diffusion of atoms through dislocations (see
 519 Fig.13e). In the deformed sample, the dislocations acted as the preferable sites for the dispersoid

520 nucleation. Due to the fast diffusion of the alloying elements and favorable nucleation conditions
 521 created by the presence of a great number of dislocations, α -Al(MnFe)Si dispersoids can also
 522 precipitate in the Mn depleted zone (formerly the DFZ) close to intermetallic particles and grain
 523 boundaries, resulting in an overall uniform dispersoid distribution by reducing the DFZs in the
 524 microstructure.

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529 **Fig. 14** Schematic diagram of the dislocation-based nucleation mechanism of α -Al(MnFe)Si
 530 dispersoids in the deformed sample, (a) metastable Mg₂Si precipitated and co-existed with
 531 dislocations; (b) metastable Mg₂Si dissolution and Si and Mn diffusion along dislocations and (c)
 532 α -Al(MnFe)Si dispersoid nucleation and growth on dislocations including in the Mn depleted
 533 zone (formerly the DFZ).

534

535 5. Conclusions

- 536 1) In Al-Mn-Mg 3xxx alloys, Mg plays an important role in promoting the formation of α -
 537 Al(MnFe)Si dispersoids. Without Mg addition, the precipitation of α -Al(MnFe)Si

538 dispersoids was so difficult that only an insufficient number of dispersoids could be obtained.
539 The number density and volume fraction of the dispersoids in the Mg containing alloy are
540 much higher than that in the base alloy without Mg, resulting in a strong dispersoid
541 strengthening effect.

542 2) During heating process of the heat treatment of the Mg containing alloy, metastable Mg_2Si
543 precipitated and dissolved, leaving local Si-rich areas, which provided favorable nucleation
544 sites for $\alpha-Al(MnFe)Si$ dispersoids. Both metastable $\beta''-Mg_2Si$ and $\beta'-Mg_2Si$ have a positive
545 effect on increasing the number density and volume fraction of the dispersoids. However,
546 equilibrium $\beta-Mg_2Si$ precipitates do not have any effect on the dispersoid formation.

547 3) $\beta'-Mg_2Si$ precipitates are more effective than $\beta''-Mg_2Si$ in promoting dispersoid nucleation.
548 It could be attributed to the fact that $\beta'-Mg_2Si$ would provide more available Si in the Si-rich
549 areas for $\alpha-Al(MnFe)Si$ nucleation and growth than $\beta''-Mg_2Si$.

550 4) In the deformed sample, the dislocations become the preferable sites for $\alpha-Al(MnFe)Si$
551 dispersoid nucleation. Due to the presence of a great number of dislocations, $\alpha-Al(MnFe)Si$
552 dispersoids can nucleate and grow in the Mn depleted zone (formerly the DFZ) close to
553 intermetallic particles and grain boundaries, resulting in a more uniform dispersoid
554 distribution compared to the non-deformed sample.

555 5) The dispersoid nucleation mechanisms based on both metastable Mg_2Si and dislocations are
556 proposed and discussed.

557

558 **Acknowledgments**

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614 **Tables**

615

616

Table 1 Chemical composition of experimental alloys (wt%)

Alloy code	Si	Fe	Mn	Mg	Al
Base	0.23	0.56	1.23	0.002	Bal.
M1	0.26	0.57	1.25	1.00	Bal.

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Table 2 Dispersoid and DFZ parameters measured under different conditions

Alloy	Heat treatment	Area fraction of DFZ (%)	Equivalent diameter of dispersoids (nm)	Number density of dispersoids (μm^{-3})	Volume fraction of dispersoids (%)
Base	648K(375°C)/24h	79	97	72	0.32
Base	648K(375°C)/24h	51.4	80	-	0.82
M1 Alloy	648K(375°C)/24h	26.4	50	1055	2.69
M1 Alloy	448K(175°C)/5h + 648K(375°C)/24h	30	56	563	1.93
M1 Alloy	523K(250°C)/12h + 648K(375°C)/24h	23	42	1326	2.15
Deformed M1 Alloy	648K(375°C)/24h	7	68	294	2.58

619

620 **A List of Figure Captions**

621

622 **Fig. 1** Schematic diagram of various heat treatments (a) procedure A and (b) procedure B (two-
623 step heat treatment).

624

625 **Fig. 2** Optical images showing the dispersoid distribution in the base alloy, (a) 648 K (375 °C)
626 for 24 h and (b) 648 K (375 °C) for 72 h.

627

628 **Fig. 3** TEM bright field images showing the dispersoids in the base alloy, (a) 648 K (375 °C) for
629 24 h and (b) 648 K (375 °C) for 72 h, recorded near $[001]_{Al}$ zone axis.

630

631 **Fig. 4** Optical images showing the precipitation of dispersoids in the M1 alloy under different
632 heat treatment conditions, (a) 648K(375°C)/24h, (b) 448K(175°C)/5h + 648K(375°C)/24h and
633 (c) 523K(250°C)/12h + 648K(375°C)/24h.

634

635 **Fig. 5** TEM bright field images showing the dispersoids in the M1 alloy after different heat
636 treatments, (a) 648K(375°C)/24h, (b) 448K(175°C)/5h + 648K(375°C)/24h and (c)
637 523K(250°C)/12h + 648K(375°C)/24h, recorded near the $[001]_{Al}$ zone axis. The arrows indicate
638 the $\langle 100 \rangle_{Al}$ orientation.

639

640 **Fig. 6** Optical image showing the precipitation of dispersoids in the deformed M1 alloy after heat
641 treatment at 648K(375°C)/24h: (a) the dense dispersoid zone and the less dense dispersoid zone
642 and (b) enlarged image of (a).

643

644 **Fig. 7** TEM bright field images showing the dispersoids in the deformed M1 alloy (0.2 strain +
645 648K(375°C)/24h), a) in the dense dispersoid zone and b) in the less dense dispersoid zone.

646

647 **Fig. 8** Microhardness of the base alloy and M1 alloy under various experimental conditions.

648

649 **Fig. 9** The precipitation process in the M1 alloy (a) as-heated at 548 K (275 °C), (b) as-heated at
650 648 K (375 °C), (c) 648 K (375 °C) for 30 min, (d) 648 K (375 °C) for 1 h, (e) 648 K (375 °C) for

651 2 h, (f) the selected area diffraction pattern (SADP) corresponding to the image (a) and the
652 typical diffraction spots of β' -Mg₂Si indicated by the red circles.

653
654 **Fig. 10** TEM analysis of the M1 sample held at 648 K (375 °C) for 15 minutes showing the local
655 Si enrichment on the sites of previous β' -Mg₂Si precipitates, (a) TEM image on the site of a
656 previous β' -Mg₂Si and the position of the line scanning (A-C) and (b) Si distribution along the
657 line A-C.

658
659 **Fig. 11** TEM images of the M1 samples experienced (a) 448 K (175 °C) for 5 h, (b) 523 K (250
660 °C) for 12 h, (c) 448 K (175 °C) for 5 h + 648 K (375 °C) for 1 h, (d) 523 K (250 °C) for 12 h +
661 648 K (375 °C) for 1 h, (e) the selected area diffraction pattern (SADP) corresponding to the
662 image (a) and the typical diffraction spots of β'' -Mg₂Si indicated by the red circles, (f) the
663 selected area diffraction pattern (SADP) corresponding to the image (b) and the typical
664 diffraction spots of β' -Mg₂Si indicated by the red circles.

665
666 **Fig. 12** Schematic diagram of the dispersoid formation based on metastable Mg₂Si nucleation
667 mechanism, (a) metastable Mg₂Si precipitated, (b) Mg₂Si dissolved forming Si-rich areas and (c)
668 α -Al(MnFe)Si dispersoid nucleation and growth in the Si-rich sites of previous metastable
669 Mg₂Si along the $\langle 001 \rangle_{Al}$ direction.

670
671 **Fig. 13** The precipitation process in the deformed M1 samples (a) heated to 548 K (275 °C)
672 showing dislocations, recorded near $[011]_{Al}$; (b) heated to 548 K (275 °C) showing β' -Mg₂Si,
673 recorded near $[001]_{Al}$; (c) held at 648 K (375 °C) for 1 h, recorded near $[011]_{Al}$, (d) held at 648 K
674 (375 °C) for 1 h, recorded near $[001]_{Al}$; (e) held at 648 K (375 °C) for 24 h, recorded near
675 $[011]_{Al}$.

676
677 **Fig. 14** Schematic diagram of the dislocation-based nucleation mechanism of α -Al(MnFe)Si
678 dispersoids in the deformed sample, (a) metastable Mg₂Si precipitated and co-existed with
679 dislocations; (b) metastable Mg₂Si dissolution and Si and Mn diffusion along dislocations and (c)
680 α -Al(MnFe)Si dispersoid nucleation and growth on dislocations including in the Mn depleted
681 zone (formerly the DFZ).